

PRODUCT CHANGE NOTIFICATION



Linear Technology Corporation
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August 16, 2016

PCN#081616

Dear Sir/Madam:

Subject: Notification of Change to LTC3887/LTC3887-1 Die and Datasheet

Please be advised that Linear Technology Corporation has made enhancements to the LTC3887/LTC3887-1 product die to improve performance in the following areas:

- 1) Fix errata
- 2) Reduce power up times
- 3) Reduced TON_MIN
- 4) Reduce the ADC update period
- 5) Support I²C PMBus thresholds compatible with bus power supplies as low as 1.8 volts
- 6) Improve on-chip EEPROM robustness

The documented errata in the LTC3887 are eliminated. Refer to the following link for the current errata documents <http://cds.linear.com/docs/en/spec-notice/er3887f.pdf>.

T_{INIT}, the time required from application of VIN until the part is ready to start sequencing output rails, is reduced from a typical value of 70ms to 30ms for the LTC3887/LTC3887-1. This may allow applications to power up faster after application of VIN. This change is transparent in all applications that require sequencing of multiple power rails using multiple LTC Power System Management (PSM) parts connected in the recommended manner.

TON_MIN will be reduced from nominally 90ns to 45ns to support large step down ratios at relatively high switching frequencies. The ADC update period, T_{CONVERT}, is reduced from 100ms to 90ms, providing more timely telemetry of all monitored parameters.

I²C thresholds are reduced to support PMBus communication with other ICs using I/O interface supplies as low as 1.8 volts. The V_{IL} and V_{IH} specifications for the SDA, SCL, RUN0, RUN1, GPIO0 and GPIO1 pins are reduced from 1.4V and 2.0V, respectively, to 0.8V and 1.35V. The LTC3887/LTC3887-1 is fully compliant with PMBus 1.2. For more details, please refer to PMBus 1.2 revisions on the PMBus website <http://pmbus.org/Specifications/OlderSpecifications> and the SMBus Specification Version 2.0 at <http://smbus.org/specs/smbus20.pdf>.

The above changes are shown on the attached pages of the marked up datasheet. Error Correcting Code (ECC) is added to the internal non-volatile memory to enhance its reliability. This change is transparent to the user and requires no modifications to programming

files or system firmware. As a consequence of adding ECC, the area in the EEPROM available for fault log is reduced to 4 events. The read length of 147 bytes remains the same but the fifth and sixth events are a repeat of the fourth event if the part is reset. However, when reading the fault log from RAM, all 6 events of cyclical data are available.

The new silicon can be identified with the MFR_SPECIAL_ID, PMBus command code 0xE7, with a value of 0x470* where * is a value of 8-F.

The only change to the PWM characteristics of the LTC3887/LTC3887-1 is the reduction in TON_MIN. The die changes were qualified by performing characterization over the full operating junction temperature range and through rigorous engineering evaluation across a broad range of application conditions. The revised product will have successfully completed 1000 hours burn-in before production release. Product built using the new dice will be available for shipment with an approximate datecode of 1713.

Should you have any further questions, please feel free to contact your local Linear Technology sales person or you may contact me at 408-432-1900 ext. 2374, or by E-mail DJANI@LINEAR.COM. If I do not hear from you by October 17, 2016, we will consider this change approved by your company.

Sincerely,

Daksha Jani
Quality Assurance Engineer

ELECTRICAL CHARACTERISTICS The ● denotes the specifications which apply over the specified operating junction temperature range, otherwise specifications are at $T_A = 25^\circ\text{C}$. (Note 2) $V_{IN} = 12\text{V}$, $V_{RUN0,1} = 3.3\text{V}$, $f_{SYNC} = 500\text{kHz}$ (externally driven) unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
Input Voltage							
V_{IN}	Input Voltage Range	(Note 12)	●	4.5	24	V	
I_Q	Input Voltage Supply Current Normal Operation	$V_{RUN0,1} = 3.3\text{V}$, No Caps on TG and BG $V_{RUN0,1} = 0\text{V}$		25 20		mA mA	
V_{UVLO}	Undervoltage Lockout Threshold when $V_{IN} > 4.3\text{V}$	V_{INTVCC} Falling V_{INTVCC} Rising		3.7 3.95		V V	
T_{INIT}	Initialization Time	Time from V_{IN} Applied Until the TON_DELAY Timer Starts.		-70	30	ms	
Control Loop							
V_{OUTR0}	Full-Scale Voltage High Range Set Point Accuracy (0.6V to 5V) Resolution LSB Step Size	$V_{OUT_COMMAND} = 5.500\text{V}$ (Note 9)	● ●	5.45 -0.5	5.55 0.5	V % Bits mV	
V_{OUTR1}	Full-Scale Voltage Low Range Set Point Accuracy (0.6V to 2.5V) Resolution LSB Step Size	$V_{OUT_COMMAND} = 2.75\text{V}$ (Note 9)	● ●	2.7 -0.5	2.8 0.5	V % Bits mV	
$V_{LINEREG}$	Line Regulation	$6\text{V} < V_{IN} < 24\text{V}$	●		± 0.02	%/V	
$V_{LOADREG}$	Load Regulation	$\Delta V_{ITH} = 1.35\text{V} - 0.7\text{V}$ $\Delta V_{ITH} = 1.35\text{V} - 2.0\text{V}$	● ●	0.01 -0.01	0.1 -0.1	% %	
$g_{m0,1}$	Error Amplifier g_m	$I_{TH0,1} = 1.22\text{V}$		3		mmho	
$I_{SENSE0,1}$	Input Current	$V_{SENSE} = 5.5\text{V}$	●	± 1	± 3	μA	
$V_{SENSEIN0}$	V_{SENSE} Input Resistance to Ground	$0\text{V} \leq V_{PIN} \leq 5.5\text{V}$		41		k Ω	
$V_{SENSEIN1}$	V_{SENSE} Input Resistance to Ground	$0\text{V} \leq V_{PIN} \leq 5.5\text{V}$		37		k Ω	
V_{ILIMIT}	Resolution			3		bits	
	$V_{ILIMMAX}$	Hi Range Lo Range	● ●	68 44	75 50	82 56	mV mV
	$V_{ILIMMIN}$	Hi Range Lo Range			37.5 25	mV mV	
Gate Drivers LTC3887							
$T_{G0,1}$	TG Transition Time (LTC3887/LTC3887-1)	(Note 4)					
t_r	Rise Time	$C_{LOAD} = 3300\text{pF}$		30		ns	
t_f	Fall Time	$C_{LOAD} = 3300\text{pF}$		30		ns	
$T_{BG0,1}$	BG Transition Time:	(Note 4)					
t_r	Rise Time	$C_{LOAD} = 3300\text{pF}$		30		ns	
t_f	Fall Time	$C_{LOAD} = 3300\text{pF}$		30		ns	
TG/BG t_{1D}	Top Gate Off to Bottom Gate On Delay Time	(Note 4) $C_{LOAD} = 3300\text{pF}$ Each Driver		30		ns	
BG/TG t_{2D}	Bottom Gate Off to Top Gate On Delay Time	(Note 4) $C_{LOAD} = 3300\text{pF}$ Each Driver		30		ns	
$t_{ON(MIN)}$	Minimum On-Time (LTC3887/LTC3887-1)			-90	45	ns	
OV Output Voltage Supervisor							
N	Resolution			8		Bits	
V_{RANGE0}	Voltage Monitoring Range	Range Value = 0		1	5.6	V	
V_{RANGE1}	Voltage Monitoring Range	Range Value = 1		0.5	2.7	V	
V_{OUSTP0}	Threshold Programming Step	Range Value = 0		22.5		mV	
V_{OUSTP1}	Threshold Programming Step	Range Value = 1		11.25		mV	
V_{THACC0}	Threshold Accuracy $2\text{V} < V_{OUT} < 5\text{V}$	Range Value = 0	●		± 2	%	
V_{THACC1}	Threshold Accuracy $1\text{V} < V_{OUT} < 2.5\text{V}$	Range Value = 1	●		± 2	%	
t_{PROPOV}	OV Comparator to GPIO Low Time	$V_{OD} = 10\%$ of Threshold			35	μs	

LTC3887/LTC3887-1

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
UV Output Voltage Supervisor						
N	Resolution			8		bits
V_{RANGE0}	Voltage Range	High Range	1		5.5	V
V_{RANGE1}	Voltage Range	Low Range	0.5		2.7	V
V_{OUSTP0}	Step Size	Range Value = 0, High Range		22		mV
V_{OUSTP1}	Step Size	Range Value = 1, Low Range		11		mV
V_{THACC0}	Threshold Accuracy $2\text{V} < V_{\text{OUT}} < 5\text{V}$	Range Value = 0, High Range	●		± 2	%
V_{THACC1}	Threshold Accuracy $1\text{V} < V_{\text{OUT}} < 2.5\text{V}$	Range Value = 1, Low Range	●		± 2	%
t_{PROPUV}	UV Comparator to GPIO Low Time	$V_{\text{DD}} = 10\%$ of Threshold			100	μs
V_{IN} Voltage Supervisor						
N	Resolution			8		bits
V_{INRANGE}	Full-Scale Voltage		4.5		20	V
V_{INSTP}	Step Size			82		mV
V_{INTHACC}	Threshold Accuracy $9.0\text{V} < V_{\text{IN}} < 20\text{V}$		●		± 2.5	%
V_{INTHACCM}	Threshold Accuracy $4.5\text{V} < V_{\text{IN}} \leq 9\text{V}$		●		± 5	%
t_{PROPVIN}	Comparator Response Time ($V_{\text{IN_ON}}$ and $V_{\text{IN_OFF}}$)	$V_{\text{DD}} = 10\%$ of Threshold			100	μs
Output Voltage Readback						
N	Resolution			16		Bits
	LSB Step Size			244		μV
V_{OFS}	Full-Scale Voltage	(Note 10) $V_{\text{RUNn}} = 0\text{V}$ (Note 8)		8		V
$V_{\text{OUT_TUE}}$	Total Unadjusted Error	(Note 8) $V_{\text{OUTn}} > 0.6\text{V}$	●		0.5	%
V_{OS}	Zero-Code Offset Voltage				± 500	μV
t_{CONVERT}	Conversion Time	(Note 6)		100	90	ms
V_{IN} Voltage Readback						
N	Resolution	(Note 5)		10		Bits
V_{IFS}	Full-Scale Voltage	(Note 11)		38.91		V
$V_{\text{IN_TUE}}$	Total Unadjusted Error	$V_{\text{IN}} > 4.5\text{V}$ (Note 8)	●		0.5 2	%
t_{CONVERT}	Conversion Time	(Note 6)		100	90	ms
Output Current Readback						
N	Resolution	(Note 5)		10		Bits
	LSB Step Size	$0\text{V} \leq V_{\text{ISENSE}^+} - V_{\text{ISENSE}^-} < 16\text{mV}$ $16\text{mV} \leq V_{\text{ISENSE}^+} - V_{\text{ISENSE}^-} < 32\text{mV}$ $32\text{mV} \leq V_{\text{ISENSE}^+} - V_{\text{ISENSE}^-} < 63.9\text{mV}$ $63.9\text{mV} \leq V_{\text{ISENSE}^+} - V_{\text{ISENSE}^-} < 127.9\text{mV}$		15.625 31.25 62.5 125		μV μV μV μV
I_{FS}	Full-Scale Current	(Note 7) $R_{\text{ISENSE}} = 1\text{m}\Omega$		± 128		A
$I_{\text{OUT_TUE}}$	Total Unadjusted Error	(Note 8) $V_{\text{ISENSE}} > 6\text{mV}$	●		± 1	%
V_{OS}	Zero-Code Offset Voltage				± 28	μV
t_{CONVERT}	Conversion Time	(Note 6)		100	90	ms
Input Current and Duty Cycle Readback						
D_RES	Resolution			10		Bits
D_TUE	Total Unadjusted Error	16.3% Duty Cycle		-3	3	%
t_{CONVERT}	Update Rate	(Note 6)		100	90	ms
Temperature Readback (T0, T1, T2)						
$T_{\text{RES_T}}$	Resolution			0.25		$^\circ\text{C}$
$T0,1_TUE$	External TSNS TUE	$\Delta V_{\text{TSNS}} = 72\text{mV}$ (Note 8)	●		± 3	$^\circ\text{C}$
$T2_TUE$	Internal TSNS TUE	$V_{\text{RUN0,1}} = 0.0\text{V}$, $f_{\text{SYNC}} = 0\text{kHz}$ (Note 8)		± 1		$^\circ\text{C}$
$t_{\text{CONVERT_T}}$	Update Rate	(Note 6)		100	90	ms

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
INTV_{CC} Regulator						
V_{INTVCC}	Internal V_{CC} Voltage No Load	$6\text{V} < V_{\text{IN}} < 24\text{V}$	4.8	5	5.2	V
$V_{\text{LDO_INT}}$	INTV _{CC} Load Regulation	$I_{\text{CC}} = 0\text{mA}$ to 50mA		0.5	±2	%
V_{DD33} Regulator						
V_{DD33}	Internal V_{DD33} Voltage	$4.5\text{V} < V_{\text{INTVCC}}$	3.2	3.3	3.4	V
$I_{\text{LIM(VDD33)}}$	V_{DD33} Current Limit	$V_{\text{DD33}} = \text{GND}$		70		mA
$V_{\text{DD33_OV}}$	V_{DD33} Overvoltage Threshold			3.5		V
$V_{\text{DD33_UV}}$	V_{DD33} Undervoltage Threshold			3.1		V
V_{DD25} Regulator						
V_{DD25}	Internal V_{DD25} Voltage			2.5		V
$I_{\text{LIM(VDD25)}}$	V_{DD25} Current Limit	$V_{\text{DD25}} = \text{GND}$		50		mA
Oscillator and Phase-Locked Loop						
f_{OSC}	Oscillator Frequency Accuracy	$250\text{kHz} < f_{\text{SYNC}} < 1\text{MHz}$ Measured Falling Edge-to-Falling Edge of SYNC with SWITCH_FREQUENCY = 250.0 and 1000.0	●		±7.5	%
$V_{\text{TH,SYNC}}$	SYNC Input Threshold	V_{CLKIN} Falling V_{CLKIN} Rising		1	1.5	V
$V_{\text{OL,SYNC}}$	SYNC Low Output Voltage	$I_{\text{LOAD}} = 3\text{mA}$		0.2	0.4	V
$I_{\text{LEAK,SYNC}}$	SYNC Leakage Current in Slave Mode	$0\text{V} \leq V_{\text{PIN}} \leq 3.6\text{V}$			±5	µA
θ _{SYNC-θ0}	SYNC to Ch0 Phase Relationship Based on the Falling Edge of Sync and Rising Edge of TG0	MFR_PWM_CONFIG_LTC3887[2:0] = 0, 2, 3 MFR_PWM_CONFIG_LTC3887[2:0] = 5 MFR_PWM_CONFIG_LTC3887[2:0] = 1 MFR_PWM_CONFIG_LTC3887[2:0] = 4, 6		0	60	Deg
θ _{SYNC-θ1}	SYNC to Ch1 Phase Relationship Based on the Falling Edge of Sync and Rising Edge of TG1	MFR_PWM_CONFIG_LTC3887[2:0] = 3 MFR_PWM_CONFIG_LTC3887[2:0] = 0 MFR_PWM_CONFIG_LTC3887[2:0] = 2, 4, 5 MFR_PWM_CONFIG_LTC3887[2:0] = 1 MFR_PWM_CONFIG_LTC3887[2:0] = 6		120	180	Deg
				240	270	Deg
				300		Deg
EEPROM Characteristics						
Endurance	(Note 13)	$0^\circ\text{C} < T_J < 85^\circ\text{C}$ During EEPROM Write Operations	●	10,000		Cycles
Retention	(Note 13)	$T_J < T_{\text{JMAX}}$	●	10		Years
Mass_Write	Mass Write Operation Time	STORE_USER_ALL, $0^\circ\text{C} < T_J < 85^\circ\text{C}$ During EEPROM Write Operations	●	440	4100	ms
Digital Inputs SCL, SDA, RUN0, RUN1, GPIO0, GPIO1						
V_{IH}	Input High Threshold Voltage	SCL, SDA, RUN0, RUN1, GPIO0, GPIO1	●		2.0-1.35	V
V_{IL}	Input Low Threshold Voltage	SCL, SDA, RUN0, RUN1, GPIO0, GPIO1	●	+4-0.8		V
V_{HYST}	Input Hysteresis	SCL, SDA		0.08		V
C_{PIN}	Input Capacitance				10	pF
Digital Input WP						
I_{PUWP}	Input Pull-Up Current	WP		10		µA
Open-Drain Outputs SCL, SDA, GPIO0, GPIO1, ALERT, RUN0, RUN1, SHARE_CLK						
V_{OL}	Output Low Voltage	$I_{\text{SINK}} = 3\text{mA}$	●		0.4	V
Digital Inputs SHARE_CLK, WP						
V_{IH}	Input High Threshold Voltage			1.5	1.8	V
V_{IL}	Input Low Threshold Voltage			0.6	1	V
Leakage Current SDA, SCL, ALERT, RUN0, RUN1						
I_{OL}	Input Leakage Current	$0\text{V} \leq V_{\text{PIN}} \leq 5.5\text{V}$	●		±5	µA

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